

METHOD OF DETERMINING GATE OXIDE THICKNESS OF AN  
OPERATIONAL MOSFET

ABSTRACT OF THE INVENTION

- 5           A non-destructive and non-intrusive, user friendly, easy to setup and efficient system and method of determining the gate oxide thickness of an operational MOSFET used in real circuit applications is provided. Additionally, the present invention determines the gate oxide thickness when the operational MOSFET is operating in the inversion mode.